

IN THE CLAIMS

Please amend the claims as follows:

1. (Previously Presented) A plasma processing apparatus comprising:

a vacuum chamber including a processing region configured airtightly closable in which predetermined processing is to be applied on a substrate to be processed by action of plasma on the substrate to be processed and of which an interior is exhausted by means of an exhaust apparatus and a space separated from said processing region;

a bottom electrode provided in said vacuum chamber and configured to have the substrate to be processed placed thereon;

a top electrode provided to face said bottom electrode;

a processing gas supply mechanism configured to supply predetermined processing gas into said processing region;

a first radio-frequency power source configured to supply a radio-frequency power with a predetermined first frequency to said bottom electrode;

a second radio-frequency power source configured to supply to said bottom electrode a radio-frequency power with a second frequency that is lower than the first frequency;

a first power feeder having a first matching device that performs impedance matching for the radio-frequency power to be supplied to said bottom electrode from said first radio-frequency power source, said first power feeder being configured to feed the radio-frequency power with the first frequency to said bottom electrode from a center portion of said bottom electrode; and

a second power feeder having a second matching device that is structured as a separate body from said first matching device and performs impedance matching for the radio-frequency power to be supplied to said bottom electrode from said second radio-frequency power source, said second power feeder being configured to feed the radio-

frequency power with the second frequency to said bottom electrode from an outer peripheral portion of said bottom electrode,

wherein at least a portion of said first matching device is disposed in said space.

2. (Cancelled).

3. (Cancelled).

4. (Previously Presented) A plasma processing apparatus as set forth in claim 1, wherein said first matching device is electrically connected to said bottom electrode via a non-coaxially structured feeding rod.

5. (Previously Presented) A plasma processing apparatus as set forth in claim 1, wherein the first frequency is 13.56 MHz to 150 MHz.

6. (Previously Presented) A plasma processing apparatus as set forth in claim 1, wherein the second frequency is 0.5 MHz to 13.56 MHz.

7. (Previously Presented) A plasma processing apparatus as set forth in claim 1, wherein capacitance of said bottom electrode is set to 50 pF or less.

8. (Previously Presented) A plasma processing apparatus as set forth in claim 1, wherein the substrate to be processed is etched by the action of the plasma on the substrate to be processed.

9. (Previously Presented) A plasma processing apparatus as set forth in claim 1, comprising:

said bottom electrode being disposed on an insulator plate; and

said space being formed between said insulator plate and a bottom of said chamber.

10. (Currently Amended) A plasma processing apparatus as set forth in claim 1, comprising:

~~said a~~ non-coaxially structured feeding rod ~~being~~ located entirely within said chamber.